

Silicon NPN Power Transistors

2SC2582

DESCRIPTION

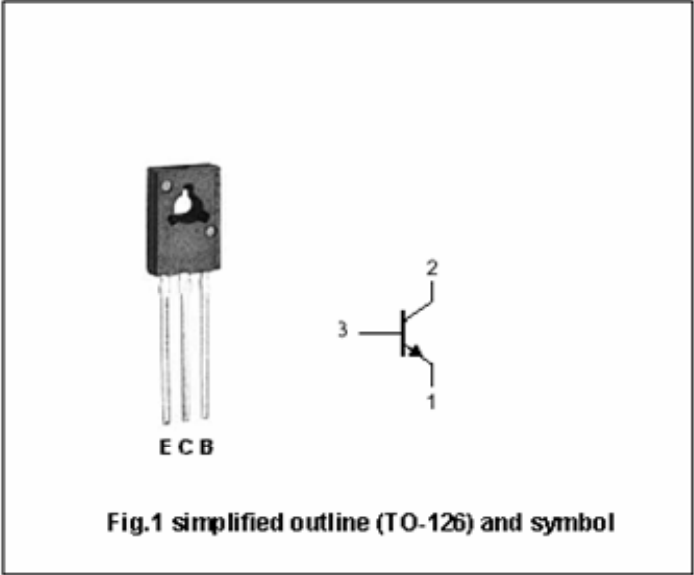
- With TO-126 package
- Large collector power dissipation
- High transition frequency

APPLICATIONS

- Audio frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		45	V
V_{CEO}	Collector- emitter voltage		35	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1	A
I_{CM}	Collector current-peak		1.5	A
P_C	Collector power dissipation	$T_a=25$	1.2	W
		$T_C=25$	10	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55 ~ +150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=2mA ; I_B=0$	35			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	45			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=500mA ; I_B=50mA$			0.5	V
I_{CEO}	Collector cut-off current	$V_{CE}=20V ; I_B=0$			100	μA
I_{CBO}	Collector cut-off current	$V_{CB}=20V ; I_E=0$			0.1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			10	μA
h_{FE-1}	DC current gain	$I_C=500mA ; V_{CE}=10V$	85		340	
h_{FE-2}	DC current gain	$I_C=1A ; V_{CE}=5V$	50			
C_{OB}	Output capacitance	$I_E=0 ; V_{CB}=10V ; f=1MHz$			20	pF
f_T	Transition frequency	$I_C=50mA ; V_{CE}=10V$		200		MHz

◆ h_{FE-1} Classifications

Q	R	S
85-170	120-240	170-340

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PACKAGE OUTLINE

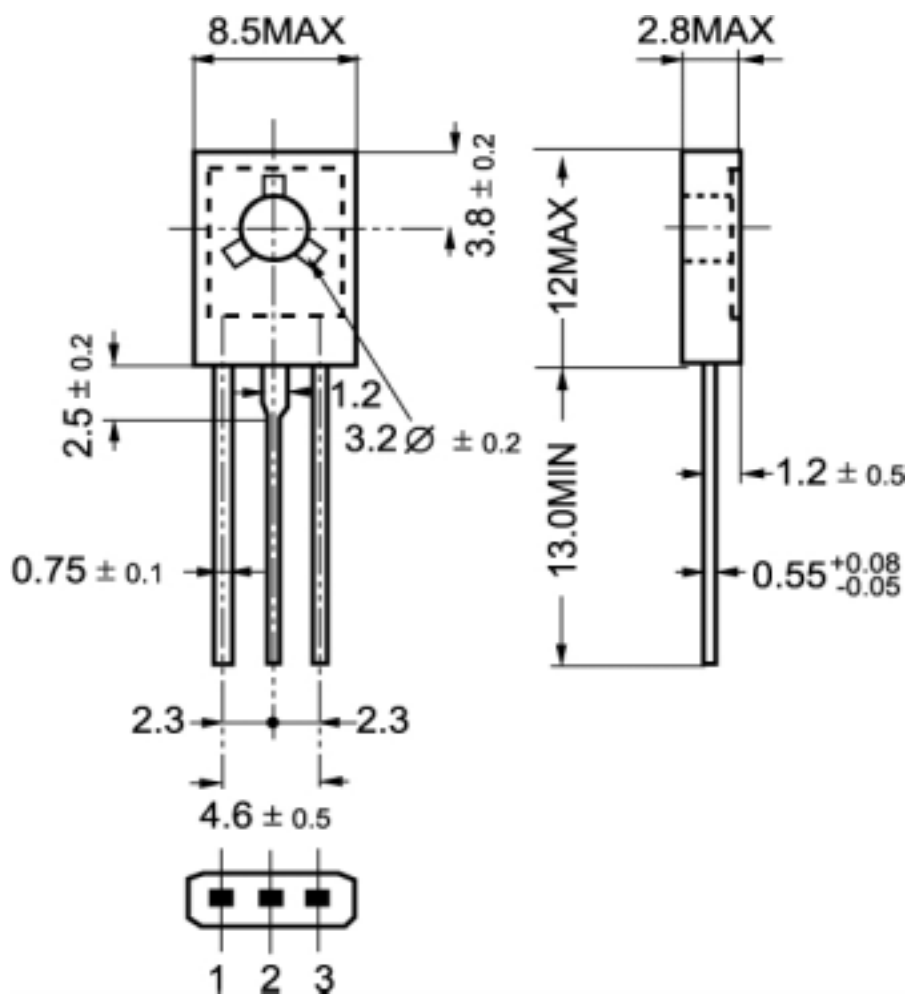


Fig.2 Outline dimensions